

ABSTRACT OF THE DISCLOSURE

In order to be able to automatically define significant measurement points for measuring the film thickness of a transparent film on a circuit pattern buried under an optically transparent thin film, in a method for determining measurement points for measuring film thickness, whereby measurement points for measuring the film thickness of optically transparent thin film on a circuit pattern formed on a wafer beneath an optically transparent thin film, are determined automatically, light is irradiated onto the surface of the wafer, either intermittently or continuously, starting at a predetermined provisional reference measurement point in the region of a particular chip on the wafer, and following a predetermined path of travel in the vicinity of this provisional reference measurement point, the light reflected by the wafer is detected, and the measurement points for measuring film thickness are determined on the basis of spectral waveform data for the reflected light thus detected.